

**IN THE CLAIMS:**

**Please cancel** claims 24-26. **Please also amend** claims 21-23 as shown in the complete list of claims that is presented below.

Claims 1-20 (cancelled).

Claim 21 (currently amended): A method for manufacturing a semiconductor device, in which a first semiconductor chip or substrate and a second semiconductor chip are joined to each other ~~with the surfaces thereof on which an~~ face-to-face via bumps provided on electrode terminals or a wiring are formed respectively as facing each other via metals of the surface of said electrode terminal or said wiring, of said first semiconductor chip or substrate and said second semiconductor chip, comprising the steps of:

providing at least one of said metals bumps with a low-melting point metal layer having a lower melting point than that of each of said metals bumps; and

superposing said first semiconductor chip or substrate and said second semiconductor chip without perfect alignment, such that one is on the other, and said bumps are facing each other;

melting said low-melting point metal layer or alloying said metals with heating up said first semiconductor chip or substrate and said second semiconductor chip to a temperature at which said low-melting point metal layer melts, to thereby self-align said second semiconductor chip or substrate and said second chip and join said first semiconductor chip or substrate and said second semiconductor chip them to each other; and

filling an insulating resin into a gap between said first semiconductor chip or substrate and said second semiconductor chip after they are joined.

Claim 22 (currently amended): ~~A~~ The method for manufacturing a semiconductor device, in which a first semiconductor chip or substrate and a second semiconductor chip are joined to each other with the surfaces thereof on which an electrode terminal or a wiring are formed respectively as facing each other via metals of the surface of said electrode terminal or said wiring, comprising the steps step of:

~~providing at least one of said metals with a low melting point metal layer having a lower melting point than that of each of said metals; and~~

liquefying said low-melting point metal layer to thereby diffuse said metals of said bumps provided on the surface of said electrode terminal or said wiring into the liquefied low-melting point metal, by the liquid-phase diffusion method, thus joining said first semiconductor chip or substrate and said second semiconductor chip to each other.

Claim 23 (currently amended): The method according to claim 22, wherein ~~said metals bumps~~ are made of Au and said low-melting point metal layer is made of an Au-Sn alloy or Sn, ~~so that said first semiconductor chip or substrate and said second semiconductor chip are superposed one on the other with said electrode terminals or said wirings thereof as facing each other and heated to a temperature at which said Au-Sn alloy or Sn melts, to be self aligned and joined with each other.~~

Claims 24-26 (cancelled).